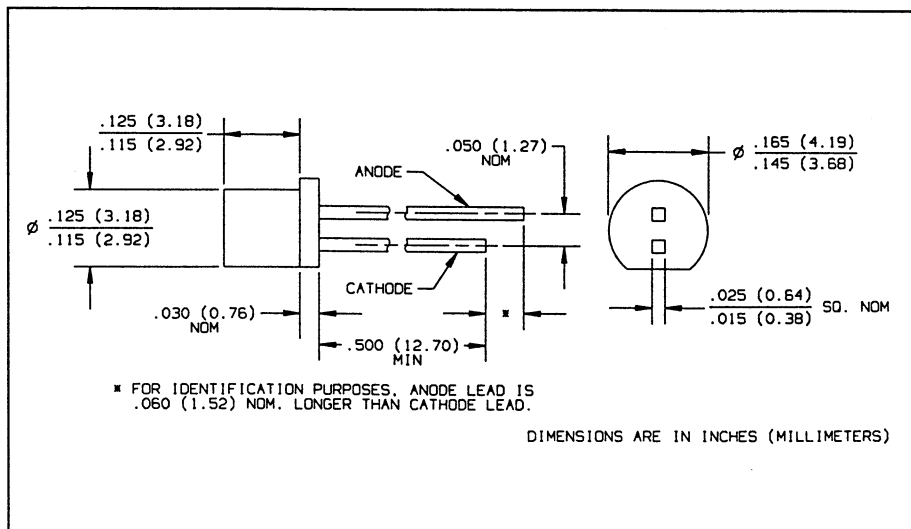
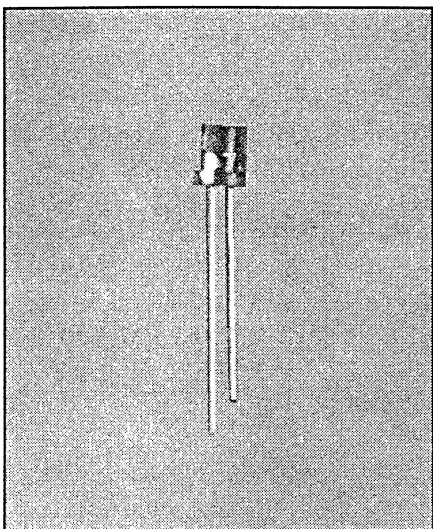


# GaAs Plastic Infrared Emitting Diode Type OP165W



## Features

- Wide irradiance pattern
- Mechanically and spectrally matched to the OP505W
- Small package size for space limited applications
- T-1 package style

## Description

The OP165W is a 935nm high intensity gallium arsenide infrared emitting diode molded in an IR transmissive amber tinted epoxy package. The broad irradiance pattern provides relatively even illumination over a large area. This package is a T-1 style in all respects except for the length of the plastic package.

## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

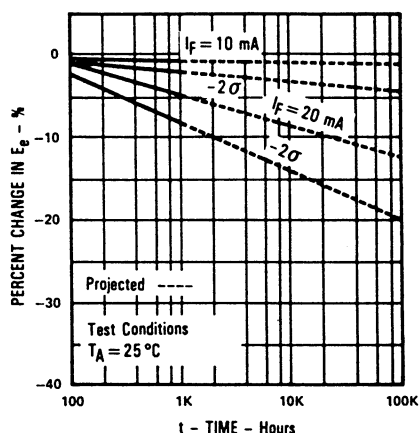
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 $\mu\text{s}$ pulse width, 300 pps)	3.0 A
Storage and Operating Temperature Range	$-40^\circ\text{C}$ to $+100^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6mm) from case for 5 sec. with soldering iron]	$260^\circ\text{C}^{(1)}$
Power Dissipation	$100\text{ mW}^{(2)}$

### Notes:

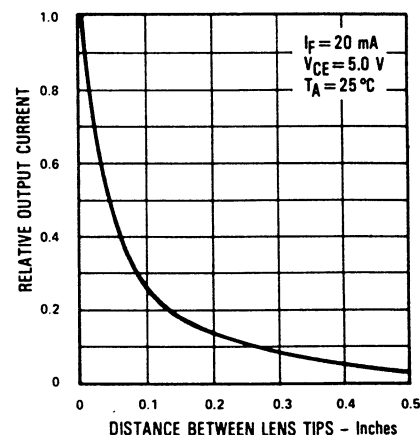
- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. A max. of 20 grams force may be applied to the leads when soldering.
- (2) Derate linearly  $1.33\text{ mW}/^\circ\text{C}$  above  $25^\circ\text{C}$ .

## Typical Performance Curves

### Percent Changes in Power Output vs Time



### Coupling Characteristics of OP165W and OP505W



# Type OP165W

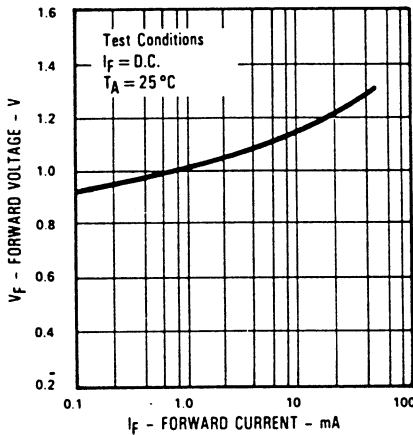
Electrical Characteristics ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
$P_O$	Radiant Power Output	0.50			mW	$I_F = 20\text{ mA}$
$V_F$	Forward Voltage			1.60	V	$I_F = 20\text{ mA}$
$I_R$	Reverse Current			100	$\mu\text{A}$	$V_R = 2.0\text{ V}$
$\lambda_p$	Wavelength at Peak Emission		935		nm	$I_F = 10\text{ mA}$
B	Spectral Bandwidth Between Half Power Points		50		nm	$I_F = 10\text{ mA}$
$\Delta\lambda_p/\Delta T$	Spectral Shift with Temperature		+0.30		$\text{nm}/^\circ\text{C}$	$I_F = \text{Constant}$
$\theta_{HP}$	Emission Angle at Half Power Points		90		Deg.	$I_F = 20\text{ mA}$
$t_r$	Output Rise Time		1000		ns	$I_{F(PK)} = 100\text{ mA}$ , $PW = 10\text{ }\mu\text{s}$ , D.C. = 10.0%
$t_f$	Output Fall Time		500		ns	

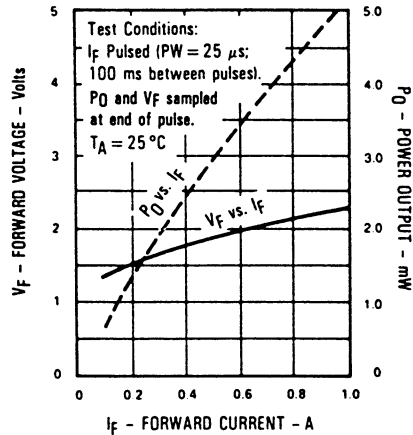
INFRARED  
EMITTING  
DIODES

## Typical Performance Curves

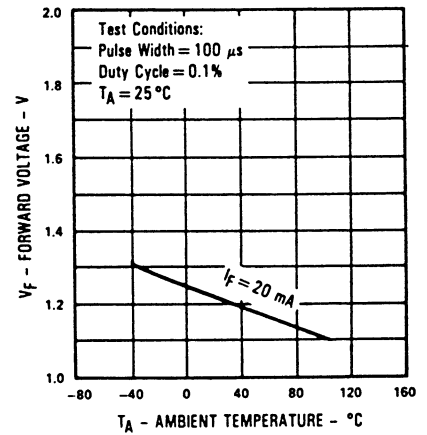
Forward Voltage vs  
Forward Current



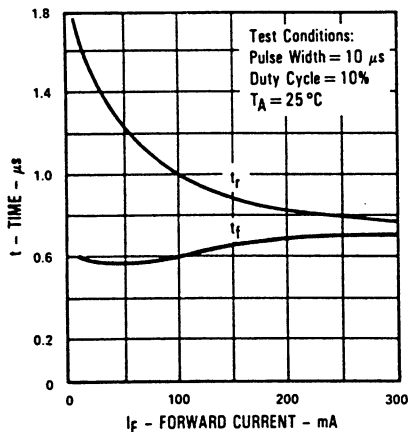
Forward Voltage and Power Output  
vs Forward Current



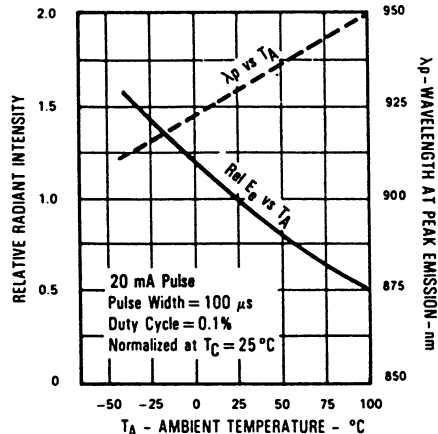
Forward Voltage vs  
Ambient Temperature



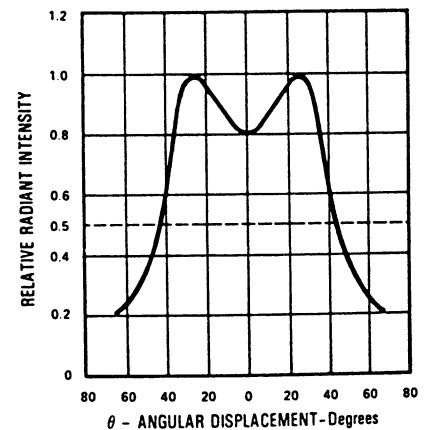
Rise Time and Fall Time vs  
Forward Current



Normalized Power Output and Wavelength  
at Peak Emission vs Ambient Temperature



Relative Radiant Intensity vs  
Angular Displacement



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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